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TOSHIBA CORPORATION

Semiconductor Company

Document Change Notification

The purpose of this notification is to inform customers about the launch of the Pb free version of the device. The introduction of a Pb-free replacement affects the datasheet. Please understand that this notification is intended as a temporary substitute for a revision of the datasheet.

Changes to the datasheet may include the following, though not all of them may apply to this particular device.

- 1. Part number
 - Example: TMPxxxxxF TMPxxxxxFG

All references to the previous part number were left unchanged in body text. The new part number is indicated on the prelims pages (cover page and this notification).

2. Package code and package dimensions

Example: LQFP100-P-1414-0.50C LQFP100-P-1414-0.50F

All references to the previous package code and package dimensions were left unchanged in body text. The new ones are indicated on the prelims pages.

3. Addition of notes on lead solderability

Now that the device is Pb-free, notes on lead solderability have been added.

4. RESTRICTIONS ON PRODUCT USE

The previous (obsolete) provision might be left unchanged on page 1 of body text. A new replacement is included on the next page.

5. Publication date of the datasheet

The publication date at the lower right corner of the prelims pages applies to the new device.

1. Part number

2. Package code and dimensions

Previous Part Number (in Body Text)	Previous Package Code (in Body Text)	New Part Number	New Package Code	OTP
TMP87PM41N	P-SDIP64-750-1.78	TMP87PM41NG	SDIP64-P-750-1.78	—
TMP87PM41F	P-QFP64-1420-1.00A	TMP87PM41FG	QFP64-P-1420-1.00A	—
TMP87PM41U	P-LQFP64-1010-0.50D	TMP87PM41UG	LQFP64-P-1010-0.50D	—

*: For the dimensions of the new package, see the attached Package Dimensions diagram.

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3. Addition of notes on lead solderability

The following solderability test is conducted on the new device.

Lead solderability of Pb-free devices (with the G suffix)

	(1) Use of Lead (Pb) ·solder bath temperature = 230°C	()
Solderability	 -dipping time = 5 seconds -the number of times = once -use of R-type flux (2) Use of Lead (Pb)-Free -solder bath temperature = 245°C -dipping time = 5 seconds -the number of times = once -use of R-type flux 	Leads with over 95% solder coverage till lead forming are acceptable.
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4. RESTRICTIONS ON PRODUCT USE

The following replaces the "RESTRICTIONS ON PRODUCT USE" on page 1 of body text.

RESTRICTIONS ON PRODUCT USE

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
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- Please contact your sales representative for product by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.
- For a discussion of how the reliability of microcontrollers can be predicted, please refer to Section 1.3 of the chapter entitled Quality and Reliability Assurance/Handling Precautions.

5. Publication date of the datasheet

The publication date of this datasheet is printed at the lower right corner of this notification.

(Annex)

Package Dimensions

SDIP64-P-750-1.78



QFP64-P-1420-1.00A

Unit: mm



LQFP64-P-1010-0.50D

Unit: mm



CMOS 8-BIT MICROCONTROLLER

TMP87PM41N, TMP87PM41F, TMP87PM41U

The 87PM41 is a One-Time PROM microcontroller with low-power 256K bits (32K bytes) electrically programmable read only memory for the 87C841/CC41/CH41/CK41/CM41 system evaluation. The 87PM41 is pin compatible with the 87C841/CC41/CH41/CK41/M41. The operations possible with the 87C841/CC41/CH41/CK41/M41 can be performed by writing programs to PROM. The 87PM41 can write and verify in the same way as the TC57256AD using an adaptor socket BM1136/BM1137/BM1121 and an EPROM programmer.





PIN FUNCTION

The 87PM41 has two modes: MCU and PROM.

(1) MCU mode

In this mode, the 87PM41 is pin compatible with the 87C841/CC41/CH41/CK41/CM41 (fix the TEST pin at low level).

(2) PROM mode

PIN NAME (PROM mode)	INPUT/OUTPUT	FUNCTIONS	PIN NAME (MCU mode)
A14 to A8	Input	PROM address inputs	P76 to P70
A7 to A0			P67 to P60
D7 to D0	Ι/Ο	PROM data input/outputs	P07 to P00
CE		Chip enable signal input (active low)	P13
ŌĒ	Input	Output enable signal input (active low)	P14
VPP		+ 12.5 V / 5 V (Program supply voltage)	TEST
vcc	Power supply	+5V	VDD
GND		ov d	VSS
P37 to P30			
P47 to P40		Pull-up with resistance for input processing	
P54 to P50	(
P11			
P21	I/O	PROM mode setting pin. Be fixed at high level.	
P77			
P17 to P15			
P12, P10		PROM mode setting pin. Be fixed at low level.	
P22, P20	\sim	r Kowi nibue setting pin. De nixed at low level.	
RESET	\sum	\sim	
XIN	Input	Connect an 8 MHz oscillator to stabilize the internal state.	
XOUT	Output		
VAREF		0.V (GND)	
VASS	Power Supply		
\sim	\sim	·	

OPERATIONAL DESCRIPTION

The following explains the 87PM41 hardware configuration and operation. The configuration and functions of the 87PM41 are the same as those of the 87C841/CC41/CH41/CK41/CM41, except in that a one-time PROM is used instead of an on-chip mask ROM.

The 87PM41 is placed in the *single-clock* mode during reset. To use the dual-clock mode, the low-frequency oscillator should be turned on by executing [SET (SYSCR2). XTEN] instruction at the beginning of the program.

1. OPERATING MODE

The 87PM41 has two modes: MCU and PROM.

1.1 MCU Mode

The MCU mode is activated by fixing the TEST / VPP pin at low level.

In the MCU mode, operation is the same as with the 87C841/CC41/CH41/CK41/CM41 (the TEST / VPP pin cannot be used open because it has no built-in pull-down resistance).

1.1.1 Program Memory

The 87PM41 has a 32 K \times 8-bit (addresses 8000_H to FFFF_H in the MCU mode, addresses 0000_H to 7FFF_H in the PROM mode) of program memory (OTP).

To use the 87PM41 as the system evaluation for the 87C841/CC41/CH41/CK41/CM41 the program should be written to the program memory area as shown the Figure 1-1.



Figure 1-1. Program Memory Area

Either write the data FF_H to the unused area or set the PROM programmer to access only the program storage area.

1.1.2 Data Memory

The 87PM41 has an on-chip 1K \times 8-bit data memory (static RAM).

1.1.3 Input/Output Circuitry

(1) Control pins

The control pins of the 87PM41 are the same as those of the 87C841/CC41/CH41/CK41/CM41 except that the TEST pin has is no built-in pull-down resistance.



(2) I/O ports

The I/O circuitries of 87PM41 I/O ports the are the same as the code A type I/O circuitries of the 87C841/CC41/CH41/CK41/CM41.

1.2 PROM Mode

The PROM mode is activated by setting the TEST, RESET pin and the ports P17 to P10, P22 to P20 and P77 as shown in Figure 1-3. The PROM mode is used to write and verify programs with a general-purpose PROM programmer. The high-speed programming mode can be used for program operation. The 87PM41 is not supported an *electric signature* mode, so the ROM type must be set to TC57256AD. Set the adaptor socket switch to "P".

Note : Please set the high-speed programming mode according to each manual of PROM.



Figure 1-3. Setting for PROM Mode

1.2.1 Programming Flowchart (High-speed Programming Mode-I)

The high-speed programming mode is achieved by applying the program voltage (+ 12.5 V) to the VPP pin when Vcc = 6 V. After the address and input data are stable, the data is programmed by applying a single 1ms program pulse to the \overline{CE} input. The programmed data is verified. If incorrect, another 1 ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. Programming for one address is ended by applying additional program pulse with width 3 times that needed for initial programming (number of programmed times \times 1 ms). After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5





1.2.2 Programming Flowchart (High-speed Programming Mode-II)

The high-speed programming mode is achieved by applying the program voltage (+ 12.75 V) to the Vpp pin when Vcc = 6.25 V. After the address and input data are stable, the data is programmed by applying a single 0.1ms program pulse to the \overline{CE} input. The programmed data is verified. If incorrect, another 0.1ms program pulse is applied and then the programmed data is verified. This process should be repeated (up to 25 times) until the program operates correctly. After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with Vcc = Vpp = 5 V.



Figure 1-5. Flowchart of High-speed Programming Mode - II

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.2.3 Writing Method for General-purpose PROM Program
(1) Adapters BM1136 : TMP87PM41N BM1137 : TMP87PM41F BM11121: TMP87PM41U
(2) Adapter setting Switch (SW1) is set to side N.
 (3) PROM programmer specifying i) PROM type is specified to TC57256D. Writing voltage: 12.5 V (high-speed program mode-I) Writing voltage: 12.75 V (high-speed program mode-II)
 ii) Data transfer (copy) (note 1) In the TMP87PM41, EPROM is within the addresses 0000_H to 7FFF_H. Data is required to b transferred (copied) to the addresses where it is possible to write. The program area in MC mode and PROM mode is referred to "Program memory area" in Figure 1-1. Ex. In the block transfer (copy) mode, executed as below. ROM capacity of 16KB : transferred addresses C000_H to FFFF_H to addresses 4000 to 7FFF_H
iii) Writing address is specified. (note 1) Start address : 0000 _H End address : 7FFF _H
 (4) Writing Writing/Verifying is required to be executed in accordance with PROM programmer operating procedure. Note 1 : The specifying method is referred to the PROM programmer description. Either write the
data FF _H to the unused area or set the PROM programmer to access only the program storage area. Note 2: When MCU is set to an adapter or the adapter is set to PROM programmer, a position of pi 1 must be adjusted. If the setting is reversed, MCU, the adapter and PROM program
damaged. Note 3 : The TMP87PP23 does not support the electric signature mode (hereinafter referred to a "signature"). If the signature is used in PROM program, a device is damaged due to applyin 12V ± 0.5V to the address pin 9 (A9). The signature must not be used.

ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATII	NGS (V	ν _{SS} = 0 V)		
PARAMETER	SYMBOL	PINS	RATINGS	UNIT
Supply Voltage	V _{DD}		-0.3 to 6.5	V
Program Voltage	V _{PP}	ТЕЅТ/VPP	-0.3 to 13.0	V
Input Voltage	V _{IN}		- 0.3 to V _{DD} + 0.3	v
Output Voltage	V _{OUT1}	$\langle () \rangle$	– 0.3 to V _{DD} + 0.3	v
	I _{OUT1}	Ports P0, P1, P2, P4, P5, P6, P7	3.2	
Output Current (Per 1 pin)	I _{OUT2}	Port P3	30	mA
	Σ Ι _{Ουτ1}	Ports P0, P1, P2, P4, P5, P6, P7	120	
Output Current (Total)	Σ Ι _{ΟUT2}	Port P3	120	mA
		TMP87PM41N	600	
Power Dissipation [Topr = 70 °C]	PD	ТМР87РМ41F, ТМР87РМ41U	350	mW
Soldering Temperature (time)	Tsld		260 (10 s)	°C
Storage Temperature	Tstg		– 55 to 125	°C
Operating Temperature	Topr		– 40 to 85	°C

PARAMETER	SYMBOL	PINS	्द	ONDITIONS	Min.	Max.	UNIT
Supply Voltage 🛛 🗸		$\left(\overline{2} \right)$	fc=8 MHz	NQRMAL1, 2 mode IDLE1, 2 mode	- 4.5		
	VDD		fc= 4.2 MHz	NORMAL1, 2 mode IDLE1, 2 mode	2.7	5.5	v
			fs=	SLOW mode SLEEP mode	2.7		
			32.700 KHZ	STOP mode	2.0		
	V _{IH1}	Except hysteresis input	>		V _{DD} × 0.70		
Input High Voltage	VIH2	VIH2 Hysteresis input		V _{DD} ≧4.5 V		V _{DD}	v
$\langle () \rangle$	V _{IH3}		\ \	√ _{DD} <4.5 ∨	V _{DD} × 0.90		
	VILI	Except hysteresis input	V _{DD} ≧4.5 V		0	V _{DD} × 0.30	
Input Low Voltage	V _{IL2}	Hysteresis input				V _{DD} × 0.25] v
	V _{IL3}		\ \	√ _{DD} <4.5 ∨		V _{DD} × 0.10	
~			V _{DD}	₉ = 4.5 to 5.5 V		8.0	D.A.L.
Clock Frequency	fc	XIN, XOUT	V _{DD} = 2.7 to 5.5 V		- 0.4	4.2	- MHz
	fs	XTIN, XTOUT			30.0	34.0	kHz

D.C. CHARACT	ERISTIC	s	$(V_{SS} = 0 V, Topr = -40 to 3)$	85 °C)				
PARAMETER	SYMBOL		PINS		Min.	Тур.	Max.	UNIT
Hysteresis Voltage	V _{HS}	Hysteresis inputs			2-	0.9	-	V
Input Current	I _{IN1} I _{IN2} I _{IN3}	<u> </u>	drain ports, Tri-state ports STOP	$V_{DD} = 5.5 V$ $V_{IN} = 5.5 V / 0 V$		<u>}</u> _	± 2	μΑ
Input Low Current	Ι _{ΙL}	Push p	ull ports	$V_{DD} = 5.5 V, V_{IN} = 0.4 V$)	-	- 2	mA
Input Resistance	R _{IN2}	RESET			90	220	510	kΩ
Output Leakage Current	I _{LO}		pen drain ports te ports	$V_{DD} = 5.5 V, V_{OUT} = 5.5 V$	-	-	2	μA
Output High Voltage	V _{OH1}	Tri-sta	te ports	$V_{DD} = 4.5 V$, $Q_{H} = -0.7 mA$	4.1	\mathcal{L}	- /	V
Output Low Voltage	V _{OL}	Except	XOUT and P3	$V_{DD} = 4.5 V_{\star} I_{OL} = 1.6 \text{ mA}$	-	\mathcal{A}	0.4	V
Output Low current	I _{OL3}	P3		$V_{DD} = 4.5 V, V_{OL} = 1.0 V$	- (20	-	mA
Supply Current in NORMAL 1, 2 modes				$V_{DD} = 5.5 V$ $V_{IN} = 5.3 V / 0.2 V$)0	16	mA
Supply Current in IDLE 1, 2 modes			(fc=8 MHz fs=32.768 kHz		4.5	6	mA
Supply Current in SLOW mode	I _{DD}		~(($V_{DD} = 3.0 V$ $V_{IN} = 2.8 V / 0.2 V$	\mathcal{P}	30	60	μA
Supply Current in SLEEP mode				fs=32.768 kHz	-	15	30	μΑ
Supply Current in STOP mode				$V_{DD} = 5.5 V$ $V_{IN} = 5.3 V / 0.2 V$	-	0.5	10	μΑ

Note 1 : Typical values show those at Topr = 25 C, $V_{DD} = 5 V$. Note 2 : Input Current I_{IN1}, I_{IN3} ; The current through resistor is not included, when the input resistor (pull-upor pull-down) is contained.

Note 3 : IDD except I_{REF}.

\sim	<					Max.		
PARAMETER	SYMBOL	CONDITIONS	Min.	Тур.	ADCDR1	ADC	DR2	UNIT
	\sim				ADCDRT	ACK = 0	ACK = 1	
	V _{AREF}		2.7	_		V _{DD}		
Analog Reference Voltage	V _{ASS}	V _{AREF} →V _{ASS} ≧2.5 V	V _{SS}	_		1.5		V
Analog Input Voltage	VAIN		V _{ASS}	_		VAREF		v
Analog Supply Current		V _{AREF} = 5.5 V V _{ASS} = 0.0 V	-	0.5		1.0		mA
Nonlinearity Error		V _{DD} = 5.0 V, V _{SS} = 0.0 V V _{AREF} = 5.000 V		_	± 1	± 3	±2	
Zero Point Error		$V_{ASS} = 0.000 V$ OR		_	± 1	± 3	± 2	
Full Scale Error		$V_{DD} = 2.7 V, V_{SS} = 0.0 V$ $V_{AREF} = 2.700 V$	_	_	± 1	± 3	±2	LSB
Total Error		$V_{ASS} = 0.000 V$	_	_	± 2	±6	±4	

A/D CONVERSION CHARACTERISTICS (Topr = -40 to 85 °C)

 Note 1 : $\triangle V_{AREF} = V_{AREF} - V_{ASS}$

 Note 2 : ADCDR1; 8 bit - A/D conversion result (1LSB = $\triangle V_{AREF}$ /256)

 ADCDR2; 10 bit - A/D conversion result (1LSB = $\triangle V_{AREF}$ /1024)

A.C. CHARACTERISTICS	(V _S	$_{\rm S}$ = 0 V, V _{DD} = 2.7 / 4.5 to 5.5 V, Top	r = - 40 to 85 °C)			
PARAMETER	SYMBOL	CONDITIONS	Min.	Typ.	Max.	UNIT
		In NORMAL1, 2 modes		\sum	10	
Machine Cycle Time		In IDLE1, 2 modes			10	
	t _{cy}	In SLOW mode		/		μs
		In SLEEP mode		-	133.3	
High Level Clock Pulse Width	t _{WCH}	For external clock operation				
Low Level Clock Pulse Width	t _{WCL}	(XIN input), fc = 8 MHz	62.5	2		> ns
High Level Clock Pulse Width	t _{WSH}	For external clock operation		A	\searrow	
Low Level Clock Pulse Width	t _{WSL}	(XTIN input), fs = 32.768 kHz		(\bigcirc)	$\overline{\bigcirc}$	μS
			(C)		9	

RECOMMEND	ED OSCILLATING C	ONDITIONS	$V_{SS} = 0 V_{\star} V_{DD} =$	2.7 / 4.5 to 5.5 V, T	opr=-40 to 8	5 °C)
		Oscillation			Recommend	ed Constant
PARAMETER	Oscillator	Frequency	Recomment	ded Oscillator	C ₁	C ₂
		8MHz	KYOCERA	KBR8.0M		
High-frequency	Ceramic Resonator	\bigcirc	KYOCERA	KBR4.0MS	30 pF	30 pF
Oscillation		4 MHz	MURATA	CSA4.00MG		
		8 MHz	тотосом	210B 8.0000		
	Crystal Oscillator	4 MHz	точосом	204B 4.0000	20 pF	20 pF
Low-frequency Oscillation	Crystal Oscillator	32.768 kHz	NDK	MX-38T	15 pF	15 pF
		\triangleleft		X <u>TIN</u>	хт <u>ои</u> т	





(2) Low-frequency Oscillation

Note: When it is used in high electrical field, an electrical shield of the package is recommended to retain normal operations.



(2) Program Operation (High speed write mode- I) (Topr = $25 \pm 5^{\circ}$ C)

PARAMETER	SYMBOL	CONDITIONS	Min.	Тур.	Max.	UNIT
Input High Voltage	V _{IH4}		V _{CC} × 0.7	-	V _{CC}	V
Input Low Voltage	VIL4		0	-	V _{CC} × 0.12	V
Power Supply Voltage	Vec	\mathcal{O}	5.75	-	6.5	V
Program Power Supply Voltage	VRP		12.0	12.5	13.0	V
Initial Program Pulse Width	t _{PW}	V _{CC} = 6.0 V ± 0.25 V V _{PP} = 12.5 V ± 0.5 V	0.95	1.0	1.05	ms



(3) Program Operation (High speed write mode -II) (Topr = $25 \pm 5 \circ$ C)

PARAMETER	SYMBOL	CONDITIONS	Min.	Тур.	Max.	UNIT
Input High Voltage	V _{IH4}	$\langle \rangle \rangle$	∀ _{CC} ×0.7		V _{CC}	V
Input Low Voltage	V _{IL4}		0	-	V _{CC} × 0.12	V
Supply Voltage	V _{CC}		6.00))	6.25	6.50	V
Program Supply Voltage	V _{PP}		12.50	12.75	13.0	V
Initial Program Pulse Width	tpw	V _{CC} = 6.25 V ± 0.25 V, V _{RP} = 12.75 V ± 0.25 V	0.095	0.1	0.105	ms



ſ	Note 1:	When V_{cc} power supply is turned on or after, V_{pp} must be increased.
		When V_{cc} power supply is turned off or before, V_{pp} must be decreased.
	Note 2:	The device must not be set to the EPROM programmer or picked up from it under applying the program voltage
		$(12.5 V \pm 0.5 V)$ to the V _{pp} pin as the device is damaged.
	Note 3:	Be sure to execute the recommended programing mode with the recommended programing adaptor. If a mode or
		an adaptor except the above, the misoperation sometimes occurs.

